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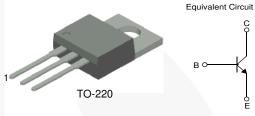


January 2014

KSC5502 NPN Planar Silicon Transistor

Features

- High-Voltage Power Switch Mode Application
- · Small Variance in Storage Time
- · Wide Safe Operating Area
- Suitable for Electronic Ballast Application



1.Base 2.Collector 3.Emitter

Ordering Information

Part Number	Marking	Package	Packing Method
KSC5502TU	J5502	TO-220	Tube

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at $T_A = 25^{\circ}\text{C}$ unless otherwise noted.

Symbol	Parameter	Value		
V _{CBO}	Collector-Base Voltage	1200	V	
V _{CEO}	Collector-Emitter Voltage	600	V	
V _{EBO}	Emitter-Base Voltage	12	V	
I _C	Collector Current (DC)	2	Α	
I _{CP}	Collector Current (Pulse) ⁽¹⁾	4	Α	
Ι _Β	Base Current (DC)	1	Α	
I _{BP}	Base Current (Pulse) ⁽¹⁾	2	Α	
T _J	Junction Temperature	150	°C	
T _{STG}	Storage Junction Temperature Range	-65 to +150	°C	
EAS	Avalanche Energy (T _J = 25°C)	2.5	mJ	

1

Notes:

1. Pulse test: pulse width = 5 ms, duty cycle ≤ 10%

Thermal Characteristics

Values are at $T_A = 25$ °C unless otherwise noted.

Symbol	Parameter	Max.	Unit
P _C	Collector Dissipation (T _C = 25°C)	50	W
$R_{\theta JC}^{(2)}$	Thermal Resistance, Junction to Case	2.5	°C/W
$R_{\theta JA}^{(3)}$	Thermal Resistance, Junction to Ambient	85	°C/W

Notes:

- 2. $R_{\theta JC}$ test fixture under infinite cooling condition.
- 3. $R_{\theta JA}$ test board and fixture under natural convection, JESD51-10 recommended thermal test board.

Electrical Characteristics(4)

Values are at $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Conditions		Min.	Тур.	Max.	Unit
BV _{CBO}	Collector-Base Breakdown Voltage	$I_C = 1 \text{ mA}, I_E = 0$		1200	1350		V
BV _{CEO} Collector-Emitter Breakdown Voltage		$I_C = 5 \text{ mA}, I_B = 0$		600	750		٧
BV _{EBO}	Emitter-Base Breakdown Voltage	$I_E = 500 \mu A, I_C = 0$		12.0	13.2		V
1	Collector Cut-Off Current	V _{CES} = 1200 V, V _{BE} = 0	$T_C = 25^{\circ}C$			100	μА
I _{CES}			$T_C = 125^{\circ}C$			500	
1	Collector Cut-Off Current	$V_{CF} = 600 \text{ V}, I_{B} = 0$	$T_C = 25^{\circ}C$			100	
I _{CEO}	Collector Gut-Oil Gurrent	VCE = 000 V, IB = 0	$T_C = 125^{\circ}C$			500	μΑ
I _{EBO}	Emitter Cut-Off Current	$V_{EB} = 12 \text{ V}, I_{C} = 0$	$T_C = 25^{\circ}C$			10	μΑ
	DC Current Gain	$V_{CF} = 1 \text{ V}, I_{C} = 0.2 \text{ A}$	$T_C = 25^{\circ}C$	15	28	40	
		$V_{CE} = 1$ V, $I_C = 0.2$ A	$T_C = 125^{\circ}C$	8	27		
h _{FE}		V _{CE} = 1 V, I _C = 1 A	$T_C = 25^{\circ}C$	4.0	8.7		
''FE			$T_C = 125^{\circ}C$	3.0	6.6		
		V _{CE} = 2.5 V, I _C = 0.5 A	$T_C = 25^{\circ}C$	12	20	30	
			$T_C = 125^{\circ}C$	6	16		
	Collector-Emitter Saturation Voltage	$I_C = 0.2 \text{ A}, I_B = 0.02 \text{ A}$	$T_C = 25^{\circ}C$		0.09	0.80	
			$T_C = 125^{\circ}C$		0.13	1.10	
V _{CE} (sat)		$I_C = 0.4 \text{ A}, I_B = 0.08 \text{ A}$	$T_C = 25^{\circ}C$		0.08	0.60	V
VCE(Sat)			$T_C = 125^{\circ}C$		0.12	1.00	
		I _C = 1 A, I _B = 0.2 A	$T_C = 25^{\circ}C$		0.19	1.50	
			$T_C = 125^{\circ}C$		0.35	3.00	
		$I_C = 0.4 \text{ A}, I_B = 0.08 \text{ A}$	$T_C = 25^{\circ}C$		0.77	1.00	
V _{BE} (sat)	Base-Emitter Saturation Voltage		$T_{C} = 125^{\circ}C$		0.65	0.90	V
V BE(Sal)		$H_{C} = 1 A$, $I_{D} = 0.2 A$	$T_C = 25^{\circ}C$		0.83	1.20	, v
			$T_{C} = 125^{\circ}C$		0.70	1.00	
C _{ib}	Input Capacitance	put Capacitance $V_{EB} = 8 \text{ V, } I_{C} = 0, f = 1 \text{ MHz}$			410	500	pF
C _{ob}	C_{ob} Output Capacitance $V_{CB} = 10 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$		1 MHz		20	100	рF

Note:

4. Pulse test : pulse width = 5 ms, duty cycle ≤ 10%

Electrical Characteristics (Continued)

Values are at $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Condition	s	Min	Тур.	Max.	Unit
	Dynamic Saturation Voltage	$I_C = 0.4 \text{ A}, I_{B1} = 80 \text{ mA},$	at 1µs		11		- V
V (DCAT)		V _{CC} = 300 V	at 3µs		8		
V _{CE} (DSAT)		$I_C = 1 \text{ A}, I_{B1} = 200 \text{ mA},$	at 1µs		23		
		$V_{CC} = 300 \text{ V}$	at 3µs		13		
Resistive L	oad Switching (D.C ≤ 10%, Pulse \	Vidth = 20 s)					
+ -	Turn-On Time	$I_C = 0.4 A,$	$T_C = 25^{\circ}C$		250	350	ne
t _{ON}		$I_{B1} = 80 \text{ mA},$ $I_{B2} = 0.2 \text{ A},$	$T_C = 125^{\circ}C$		260		ns
+ -	Turn-Off Time	$V_{CC} = 300 \text{ V},$	$T_C = 25^{\circ}C$		3.3	4.0	μs
t _{OFF}	Turi-Oil Time	$R_L = 750 \Omega$	$T_C = 125^{\circ}C$		3.8		
	Turn-On Time	I _C = 1 A,	$T_C = 25^{\circ}C$		220	450	ns
t _{ON}		I _{B1} = 160 mA,	T _C = 125°C		250		
	Turn-Off Time	I_{B2} = 160 mA, V_{CC} = 300 V, R_L = 300 Ω	T _C = 25°C		4.3	5.0	μs
t _{OFF}			T _C = 125°C		5.0		
Inductive L	oad Switching (V _{CC} = 15 V)					0	
	Storage Time	$I_{C} = 0.4 \text{ A},$ $I_{B1} = 80 \text{ mA},$ $I_{B2} = 0.2 \text{ A},$ $V_{7} = 300 \text{ V},$	$T_C = 25^{\circ}C$		1.4	2.0	
t _{STG}			T _C = 125°C		1.7		μS
	Fall Time		T _C = 25°C		130	200	ns
t _F			T _C = 125°C		80		
	0	$L_{\rm C} = 200 \mu \text{H}$	T _C = 25°C		210	350	
t _C	Cross-Over Time		T _C = 125°C		130		ns
	Ctavasa Tima		$T_C = 25^{\circ}C$		4.9	5.5	
t _{STG}	Storage Time	$I_C = 0.8 A,$	T _C = 125°C		5.3		μs
	Fall Time	I _{B1} = 160 mA,	T _C = 25°C		170	250	
t _F		$I_{B2} = 160 \text{ mA},$ $V_{CC} = 300 \text{ V},$	T _C = 125°C		340		ns
+	Cross Over Time	L _C = 200 μH	T _C = 25°C	-/	300	600	no
t _C	Cross-Over Time		T _C = 125°C		810		ns

Typical Performance Characteristics

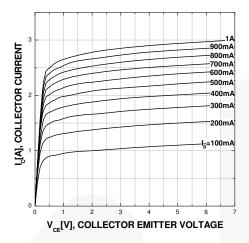


Figure 1. Static Characteristic

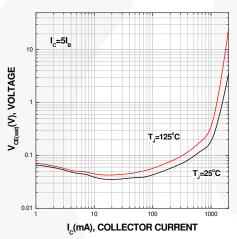


Figure 3. Collector-Emitter Saturation Voltage

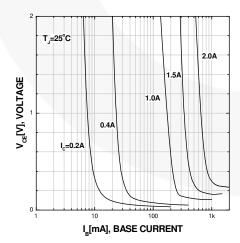


Figure 5. Typical Collector Saturation Voltage

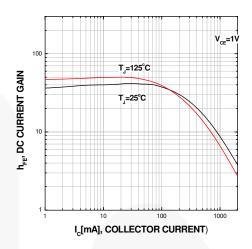


Figure 2. DC current Gain

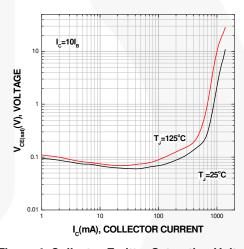


Figure 4. Collector-Emitter Saturation Voltage

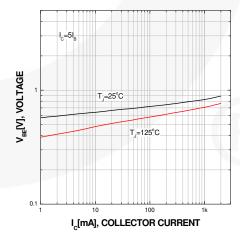


Figure 6. Base-Emitter Saturation Voltage

Typical Performance Characteristics (Continued)

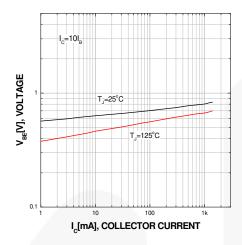


Figure 7. Base-Emitter Saturation Voltage

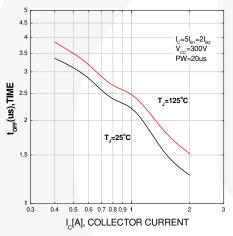


Figure 9. Resistive Switching Time, toff

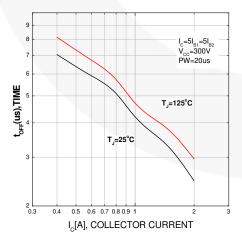


Figure 11. Resistive Switching Time, toff

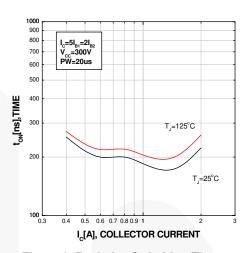


Figure 8. Resistive Switching Time, ton

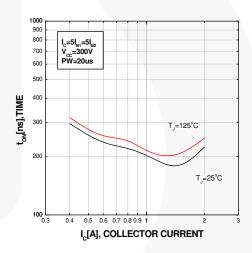


Figure 10. Resistive Switching Time, ton

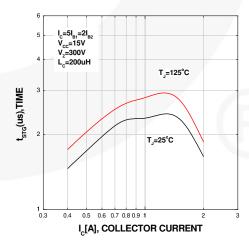


Figure 12. Inductive Switching Time, t_{STG}

Typical Performance Characteristics (Continued)

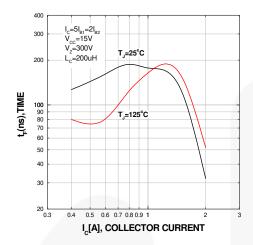


Figure 13. Inductive Switching Time, t_F

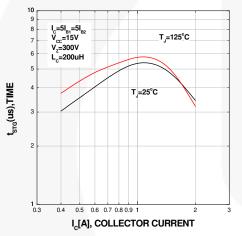


Figure 15. Inductive Switching Time, t_{STG}

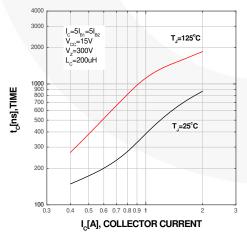


Figure 17. Inductive Switching Time, t_c

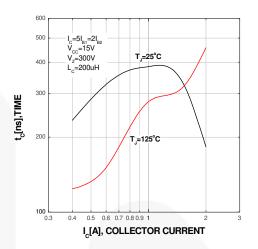


Figure 14. Inductive Switching Time, t_c

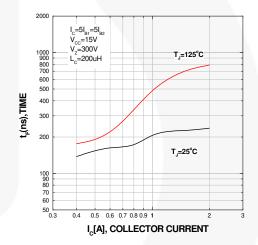


Figure 16. Inductive Switching Time, t_F

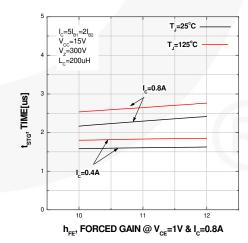


Figure 18. Inductive Switching Time, t_{STG}

Typical Performance Characteristics (Continued)

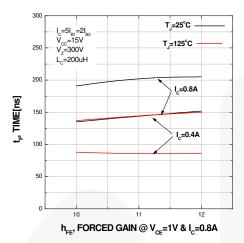


Figure 19. Inductive Switching Time, t_F

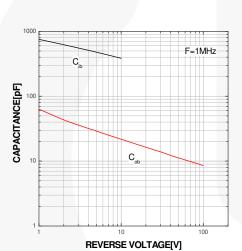


Figure 21. Capacitance

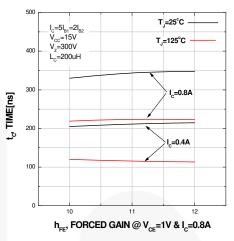


Figure 20. Inductive Switching Time, t_c

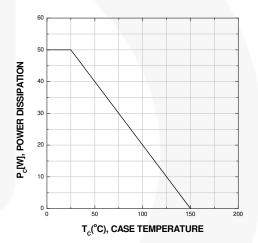


Figure 22. Power Derating

Physical Dimensions

TO-220

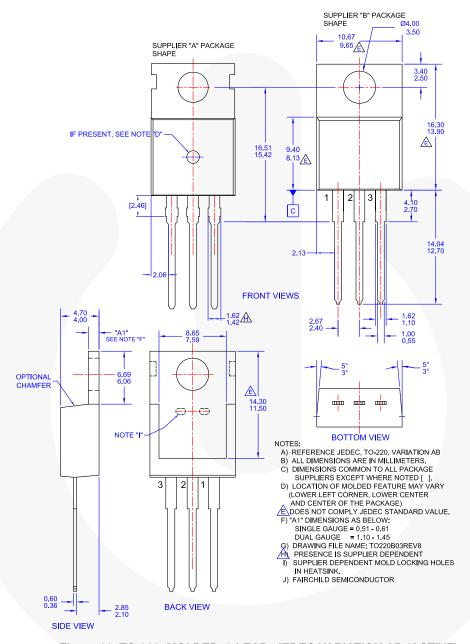


Figure 23. TO-220, MOLDED, 3-LEAD, JEDEC VARIATION AB (ACTIVE)

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Definition of Terms

Delinition of Terms		
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No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
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